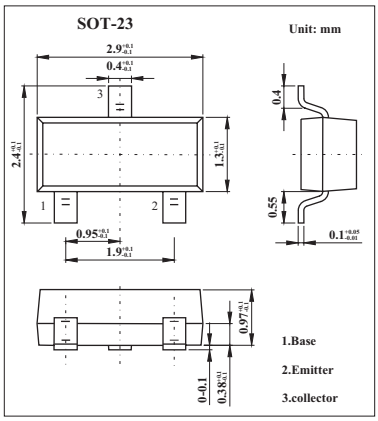
Silicon PNP Epitaxial

2SA1235



■ Features

- Small collector to emitter saturation voltage.
- Excelent lineary DC forward current gain.
- Super mini package for easy mounting.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-50	V
Collector-emitter voltage	V_{CEO}	-50	V
Emitter-base voltage	V_{EBO}	-6	V
Collector current	I_C	-200	mA
Collector dissipation (Ta=25℃)	P_C	150	mW
Jumction temperature	T_j	125	℃
Storage temperature	T_{stg}	-55 to +125	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C = -100μA , R_{BE} = ∞	-50			V
Collector cutoff current	I_{CBO}	I_{CB} = -50V , I_E = 0			-0.1	μA
Emitter cutoff current	I_{EBO}	V_{EB} = -6V , I_C = 0			-0.1	μA
DC current gain	h_{FE}	V_{CE} = -6V , I_C = -1mA	150		800	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C = -100mA , I_B = -10mA			-0.3	V
Current gain bandwidth product	f_T	V_{CE} = -6V , I_E = 10mA		200		MHz
Collector output capacitance	C_{ob}	V_{CB} = -6V , I_E = 0 , f = 1MHz		4.0		pF
Noise figure	NF	V_{CB} = -6V , I_E = 0.3mA , f = 100Hz , RG = 10KΩ			20	dB

■ h_{FE} Classification

Marking	ME	MF	MG
hFE	150～300	250～500	400～800